

S.J. Pearton J.W. Corbett  
M. Stavola

# Hydrogen in Crystalline Semiconductors



With 250 Figures

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# Contents

<b>1. Introduction</b> . . . . .	1
<b>2. Hydrogen Incorporation in Crystalline Semiconductors</b> . . . . .	4
2.1 Techniques for Hydrogen Incorporation in Semiconductors . . . . .	5
2.1.1 Hydrogen Plasma Exposure . . . . .	5
2.1.2 Hydrogen Implantation . . . . .	9
2.2 Survey of the Configurations of Hydrogen in Semiconductors . . . . .	10
2.2.1 Silicon . . . . .	10
2.2.2 Germanium . . . . .	25
2.2.3 Gallium-Arsenide and Other Compound Semiconductors . . . . .	27
<b>3. Passivation of Deep Levels by Hydrogen</b> . . . . .	28
3.1 Deep-Level Passivation in Silicon . . . . .	29
3.1.1 Metallic Impurities . . . . .	29
3.1.2 Chalcogenides . . . . .	36
3.1.3 Oxygen-Related Thermal Donors . . . . .	38
3.1.4 Process-Related Defects . . . . .	41
3.1.5 Crystalline Defects . . . . .	46
3.1.6 Thermal Stability of Passivation . . . . .	47
3.1.7 Prehydrogenation . . . . .	49
3.1.8 Models for Deep-Level Passivation . . . . .	50
3.2 Passivation of Defects in Gallium Arsenide . . . . .	52
3.3 Aluminum Gallium Arsenide . . . . .	54
3.4 Gallium Phosphide . . . . .	57
3.5 CdHgTe, Zn <sub>3</sub> P <sub>2</sub> . . . . .	57
3.6 Germanium . . . . .	58
<b>4. Shallow Impurity Passivation by Atomic Hydrogen</b> . . . . .	63
4.1 Silicon . . . . .	63
4.1.1 Silicon Acceptors . . . . .	63
4.1.2 Donors . . . . .	74
4.2 Gallium Arsenide . . . . .	83
4.2.1 Donors . . . . .	83
4.2.2 Charge States . . . . .	88
4.2.3 Acceptors . . . . .	93

4.3	AlGaAs	95
4.4	CdTe and ZnTe	96
4.5	Gallium Phosphide	97
4.6	Germanium	98
4.7	Indium Phosphide	99
4.8	BN and BP	100
4.9	Correlation with Muonium	101
<b>5. Microscopic Properties of Hydrogen-Related</b>		
	<b>Complexes in Silicon from Vibrational Spectroscopy</b>	102
5.1	Vibrational Spectroscopy of H-Related Complexes	102
5.1.1	Local Vibrational Modes	102
5.1.2	H-Stretching Vibrations of the Acceptor-H Complexes	103
5.1.3	Local Mode of the B-H Complex and the Effect of B Isotopic Substitutions	107
5.1.4	Vibrational Spectroscopy of Donor-H Complexes in Silicon	110
5.1.5	IR Studies of Lattice Defects Decorated with Hydrogen	115
5.2	Uniaxial Stress Studies of H-Related Complexes	121
5.2.1	Uniaxial Stress and Defect Symmetry	121
5.2.2	Vibrational Spectra of the B-H Complex Under Stress	122
5.2.3	Stress Studies of Donor-H Complexes	125
5.2.4	Uniaxial Stress Studies of Proton-Implanted Silicon	126
5.3	Hydrogen Motion in the B-H Complex	128
5.3.1	Kinetics of Defect Motion	129
5.3.2	IR Studies of the Reorientation of the B-H Complex	130
5.3.3	Raman Studies of the Reorientation of the B-H Complex	131
5.3.4	Tunneling vs Classical Hydrogen Motion	132
5.4	Conclusion	135
<b>6. The Microscopic Characteristics of Impurity-</b>		
	<b>Hydrogen Complexes in III-V Semiconductors</b>	137
6.1	Acceptor-H Complexes	137
6.1.1	H Complexed with Acceptors on the Group-III Sublattice	138
6.1.2	H Complexed with Acceptors on the Group-V Sublattice	142
6.2	Donor-H Complexes	143
6.2.1	GaAs:Si <sub>Ga</sub> -H	144
6.2.2	GaAs:Sn <sub>Ga</sub> -H	145
6.2.3	AlGaAs:Si-H	147

6.2.4	Donor Dependence of the Vibrational Frequencies . . . . .	148
6.3	Unintentional Hydrogenation . . . . .	148
6.4	Uniaxial Stress Studies . . . . .	151
6.4.1	GaAs:Be-H . . . . .	151
6.4.2	GaAs:Si <sub>Ga</sub> -H . . . . .	153
6.4.3	Unintentional Complexes . . . . .	153
6.5	Cluster Calculations for H-Related Complexes in GaAs . . . . .	154
6.5.1	Isolated H . . . . .	154
6.5.2	Be-H Complexes . . . . .	155
6.5.3	Si <sub>Ga</sub> -H Complexes . . . . .	155
6.6	Conclusion . . . . .	156
<b>7.</b>	<b>Hydrogen, and Semiconductor Surfaces and Surface Layers . . . . .</b>	<b>157</b>
7.1	Etching of Silicon Surfaces by Hydrogen . . . . .	157
7.2	Plasma Etching . . . . .	159
7.2.1	Dry Etching of Silicon . . . . .	159
7.2.2	Dry Etching of GaAs and InP . . . . .	163
7.3	Implantation of Protons . . . . .	164
7.3.1	Silicon . . . . .	164
7.3.2	Gallium Arsenide . . . . .	167
7.4	Hydrogen on Semiconductor Surfaces . . . . .	169
7.4.1	Silicon Surfaces . . . . .	169
7.4.2	Gallium Arsenide Surfaces . . . . .	170
7.4.3	Indium Phosphide Surfaces . . . . .	172
<b>8.</b>	<b>Hydrogen-Related Defects in Semiconductors . . . . .</b>	<b>175</b>
8.1	Hydrogen-Related Defects in Silicon . . . . .	175
8.1.1	Electron-Irradiation of Si(H) . . . . .	175
8.1.2	Proton or Neutron Irradiation of Silicon . . . . .	178
8.1.3	Implant-Induced Levels in Silicon . . . . .	182
8.1.4	Shallow H-Related Donors in Silicon . . . . .	182
8.2	Hydrogen-Related Defects in Germanium . . . . .	185
8.3	Hydrogen-Related Defects in Compound Semiconductors . . . . .	187
8.4	Hydrogen-Related IR Bands in Silicon . . . . .	188
<b>9.</b>	<b>Diffusion of Hydrogen in Semiconductors . . . . .</b>	<b>200</b>
9.1	Diffusion of Hydrogen in Solids . . . . .	200
9.2	Diffusion Equations . . . . .	202
9.3	Analysis of Diffusion Profiles . . . . .	205
9.3.1	Effects of Charge States . . . . .	206
9.3.2	Effect of Molecule Formation . . . . .	208
9.3.3	Effect of Hydrogen Trapping . . . . .	210
9.3.4	Effects of Multiple Trapping . . . . .	214
9.3.5	Comparison of Theory and Experiment . . . . .	217
9.4	Diffusion of Hydrogen in Silicon . . . . .	220
9.4.1	Early Diffusion Experiments . . . . .	221

9.4.2	Experimentally Determined Diffusivities . . . . .	223
9.4.3	Additional Features of Hydrogen Diffusion . . . . .	226
9.4.4	Rapid Diffusion of Compensating Species During Polishing . . . . .	231
9.4.5	Charge States and Hydrogen Diffusion . . . . .	232
9.4.6	Theoretical Treatments of Diffusion Paths . . . . .	234
9.4.7	Summary of Diffusion Behavior . . . . .	242
9.5	Diffusion of Hydrogen in Germanium . . . . .	246
9.6	Diffusion in Gallium Arsenide . . . . .	247
9.6.1	Dependence of Diffusion on Experimental Conditions . . . . .	248
9.6.2	Effect of Charge on Hydrogen Diffusion . . . . .	250
9.7	Diffusion of Hydrogen in Other Materials . . . . .	255
9.8	Summary . . . . .	255
<b>10.</b>	<b>Resonance Studies Pertinent to Hydrogen in Semiconductors . . . . .</b>	<b>258</b>
10.1	Electron Paramagnetic Resonance . . . . .	258
10.1.1	Theory of Electron Paramagnetic Resonance . . . . .	258
10.1.2	Experimental EPR Studies . . . . .	262
10.2	Related Muon Studies . . . . .	263
10.2.1	Use of Muon Spectroscopy . . . . .	264
10.2.2	Comparison of Theory and Experiment . . . . .	266
10.3	Perturbed Angular Correlation . . . . .	271
10.3.1	Experimental PAC Studies . . . . .	274
10.3.2	Role of Copper in Silicon . . . . .	280
<b>11.</b>	<b>Prevalence of Hydrogen Incorporation and Device Applications . . . . .</b>	<b>282</b>
11.1	Experimental Studies of Hydrogen Incorporation . . . . .	282
11.1.1	Hydrogen in Silicon Dioxide . . . . .	283
11.1.2	Bias Application to Diode Structures . . . . .	284
11.1.3	Injection of Hydrogen by Chemical Etching . . . . .	288
11.1.4	Hydrogen Injection by Ion Bombardment . . . . .	292
11.1.5	Hydrogen Injection During Metal Deposition . . . . .	296
11.1.6	Wafer Polishing . . . . .	297
11.1.7	Boiling in Water . . . . .	302
11.1.8	Proton Implantation . . . . .	305
11.1.9	Hydrogen in As-Received Wafers . . . . .	307
11.2	Hydrogen Sensing with MOS Structures . . . . .	308
11.3	Hydrogen in III-V Semiconductors . . . . .	308
11.3.1	As-Grown Material . . . . .	309
11.3.2	Annealing in Hydrogen . . . . .	311
11.3.3	Ion-Beam Processing . . . . .	312
11.3.4	Device Applications . . . . .	316

<b>12. Hydrogen and the Mechanical Properties</b>	
<b>of Semiconductors</b>	319
12.1 Hydrogen Embrittlement	319
12.1.1 Reconstruction in the Presence of Hydrogen	320
12.1.2 Defect Aggregation	324
12.2 Hydrogen-Related Defects	326
12.2.1 Plasma-Induced Defects	328
12.2.2 Theoretical Treatments	
of Hydrogen-Induced Defects	328
12.3 III-V Semiconductors	330
<b>References</b>	331
<b>Subject Index</b>	361